



VN920 VN920-B5 / VN920SO

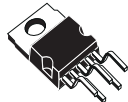
SINGLE CHANNEL HIGH SIDE SOLID STATE RELAY

TYPE	$R_{DS(on)}$	I_{OUT}	V_{CC}
VN920			
VN920-B5	16mΩ	30 A	36 V
VN920SO			

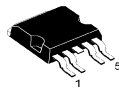
- CMOS COMPATIBLE INPUT
- PROPORTIONAL LOAD CURRENT SENSE
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- OVERVOLTAGE CLAMP
- THERMAL SHUTDOWN
- CURRENT LIMITATION
- PROTECTION AGAINST LOSS OF GROUND AND LOSS OF V_{CC}
- VERY LOW STAND-BY POWER DISSIPATION
- REVERSE BATTERY PROTECTION (*)

DESCRIPTION

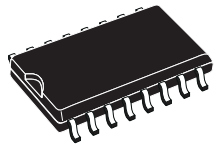
The VN920, VN920-B5, VN920SO is a monolithic device made by using STMicroelectronics VIPower M0-3 Technology, intended for driving any kind of load with one side connected to



PENTAWATT



P²PAK

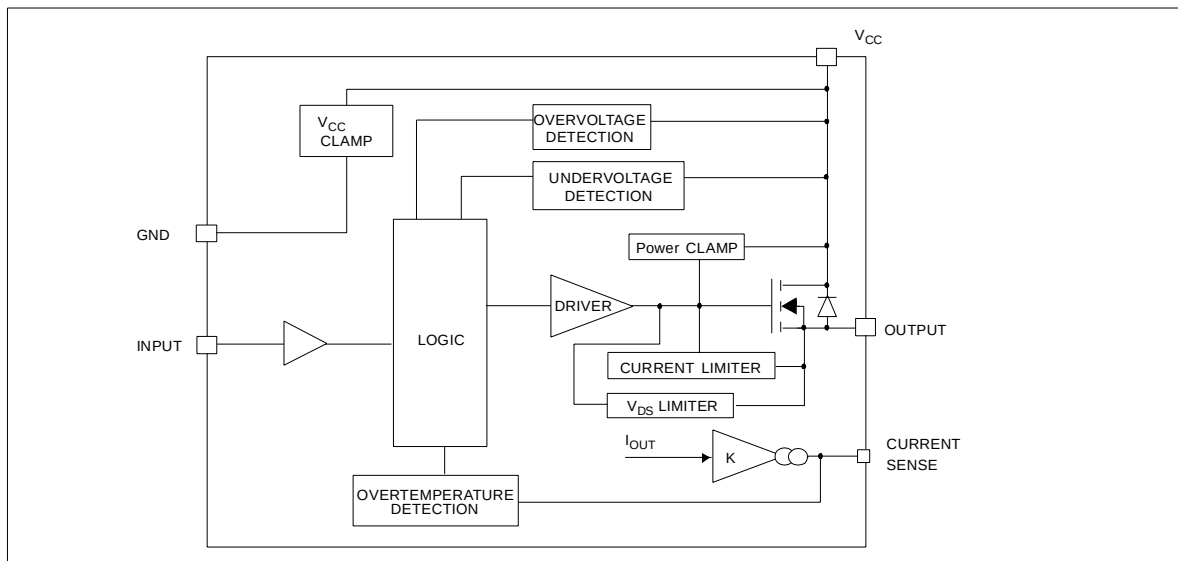


SO-16L

ORDER CODES		
PACKAGE	TUBE	T&R
PENTAWATT	VN920	-
P ² PAK	VN920-B5	VN920-B513TR
SO-16L	VN920SO	VN920SO13TR

ground. Active V_{CC} pin voltage clamp protects the device against low energy spikes (see ISO7637 transient compatibility table). Active current limitation combined with thermal shutdown and automatic restart protect the device against overload. The device integrates an analog current sense output which delivers a current proportional to the load current. Device automatically turns off in case of ground pin disconnection.

BLOCK DIAGRAM

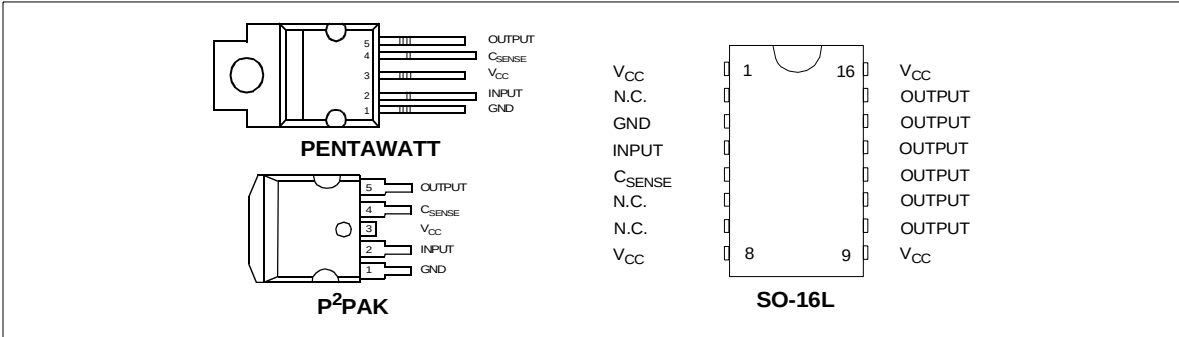


(*) See application schematic at page 8

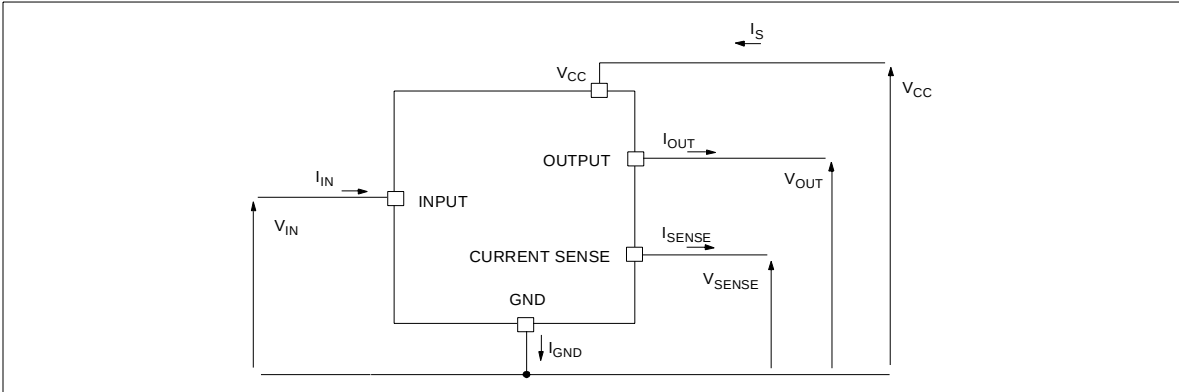
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value			Unit
		PENTAWATT	P ² PAK	SO-16L	
V_{CC}	DC Supply Voltage	41			V
$-V_{CC}$	Reverse DC Supply Voltage	- 0.3			V
$-I_{GND}$	DC Reverse Ground Pin Current	- 200			mA
I_{OUT}	DC Output Current	Internally Limited			A
$-I_{OUT}$	Reverse DC Output Current	- 21			A
I_{IN}	DC Input Current	+/- 10			mA
V_{CSense}	Current Sense Maximum Voltage	-3			V
		+15			V
V_{ESD}	Electrostatic Discharge (Human Body Model: R=1.5K Ω ; C=100pF)				
	- INPUT	4000			V
	- CURRENT SENSE	2000			V
	- OUTPUT	5000			V
	- V_{CC}	5000			V
E_{MAX}	Maximum Switching Energy (L=0.25mH; R _L =0 Ω ; V _{bat} =13.5V; T _{jstart} =150°C; I _L =45A)		364	352	mJ
P_{TOT}	Power Dissipation T _C ≤25°C	96.1	96.1	8.3	W
T_j	Junction Operating Temperature	Internally limited			°C
T_c	Case Operating Temperature	- 40 to 150			°C
T_{STG}	Storage Temperature	- 55 to 150			°C

CONNECTION DIAGRAM (TOP VIEW)



CURRENT AND VOLTAGE CONVENTIONS



THERMAL DATA

Symbol	Parameter		Value			Unit
			PENTAWATT	P ² PAK	SO-16L	
R _{thj-case}	Thermal Resistance Junction-case	Max	1.3	1.3		°C/W
R _{thj-lead}	Thermal Resistance Junction-lead	Max			15	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	61.3	51.3 (*)	65 (**)	°C/W

(*) When mounted on a standard single-sided FR-4 board with 0.5cm² of Cu (at least 35μm thick).

(**) When mounted on a standard single-sided FR-4 board with 0.5cm² of Cu (at least 35μm thick) connected to all V_{CC} pins.

ELECTRICAL CHARACTERISTICS (8V < V_{CC} < 36V; -40°C < T_j < 150°C unless otherwise specified)

POWER

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{CC}	Operating Supply Voltage		5.5	13	36	V
V _{USD}	Undervoltage Shut-down		3	4	5.5	V
V _{OV}	Overvoltage Shut-down		36			V
R _{ON}	On State Resistance	I _{OUT} =10A; T _j =25°C			16	mΩ
		I _{OUT} =10A			32	mΩ
		I _{OUT} =3A; V _{CC} =6V			55	mΩ
V _{clamp}	Clamp Voltage	I _{CC} =20mA (See note 1)	41	48	55	V
I _S	Supply Current	Off State; V _{CC} =13V; V _{IN} =V _{OUT} =0V		10	25	μA
		Off State; V _{CC} =13V; V _{IN} =V _{OUT} =0V; T _j =25°C		10	20	μA
		On State; V _{CC} =13V; V _{IN} =5V; I _{OUT} =0A; R _{SENSE} =3.9KΩ			5	mA
I _{L(off1)}	Off State Output Current	V _{IN} =V _{OUT} =0V	0		50	μA
I _{L(off2)}	Off State Output Current	V _{IN} =0V; V _{OUT} =3.5V	-75		0	μA
I _{L(off3)}	Off State Output Current	V _{IN} =V _{OUT} =0V; V _{CC} =13V; T _j =125°C			5	μA
I _{L(off4)}	Off State Output Current	V _{IN} =V _{OUT} =0V; V _{CC} =13V; T _j =25°C			3	μA

SWITCHING (V_{CC}=13V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t _{d(on)}	Turn-on Delay Time	R _L =1.3Ω (see figure 2)		50		μs
t _{d(off)}	Turn-off Delay Time	R _L =1.3Ω (see figure 2)		50		μs
dV _{OUT} /dt _(on)	Turn-on Voltage Slope	R _L =1.3Ω (see figure 2)		See relative diagram		V/μs
dV _{OUT} /dt _(off)	Turn-off Voltage Slope	R _L =1.3Ω (see figure 2)		See relative diagram		V/μs

LOGIC INPUT

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{IL}	Input Low Level				1.25	V
I _{IL}	Low Level Input Current	V _{IN} =1.25V	1			μA
V _{IH}	Input High Level		3.25			V
I _{IH}	High Level Input Current	V _{IN} =3.25V			10	μA
V _{I(hyst)}	Input Hysteresis Voltage		0.5			V
V _{ICL}	Input Clamp Voltage	I _{IN} =1mA	6	6.8	8	V
		I _{IN} =-1mA		-0.7		V

Note 1: V_{clamp} and V_{OV} are correlated. Typical difference is 5V.

ELECTRICAL CHARACTERISTICS (continued)CURRENT SENSE ($9V \leq V_{CC} \leq 16V$) (See Fig. 1)

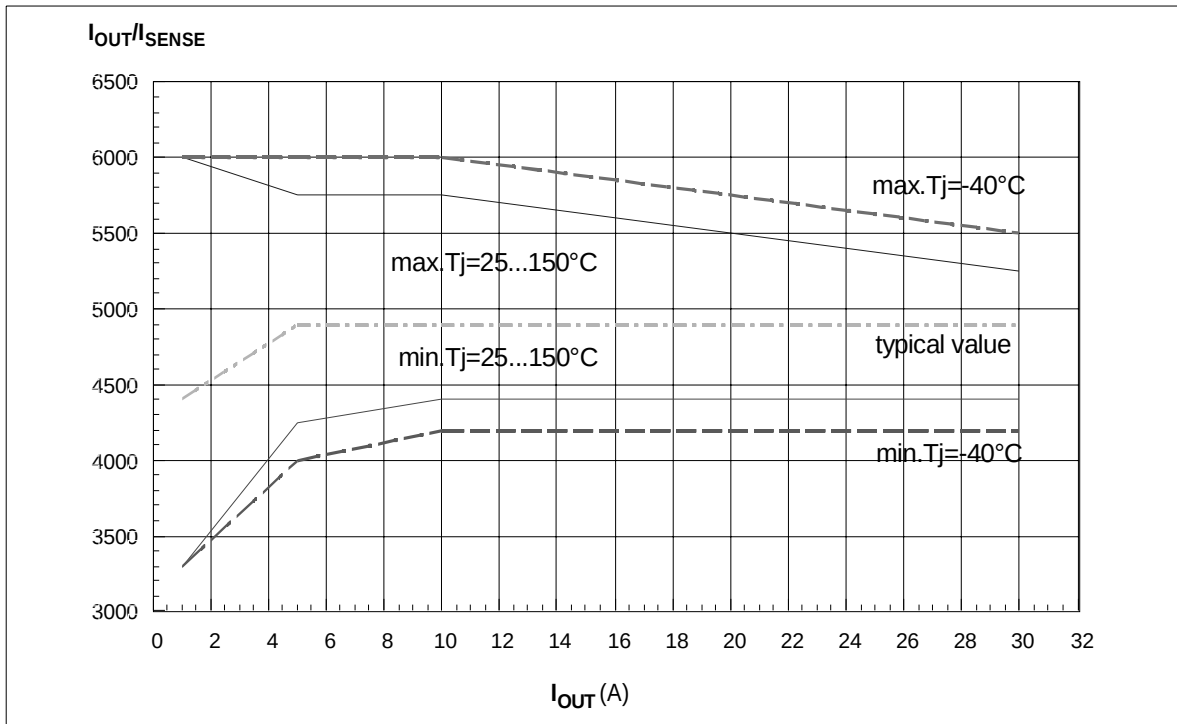
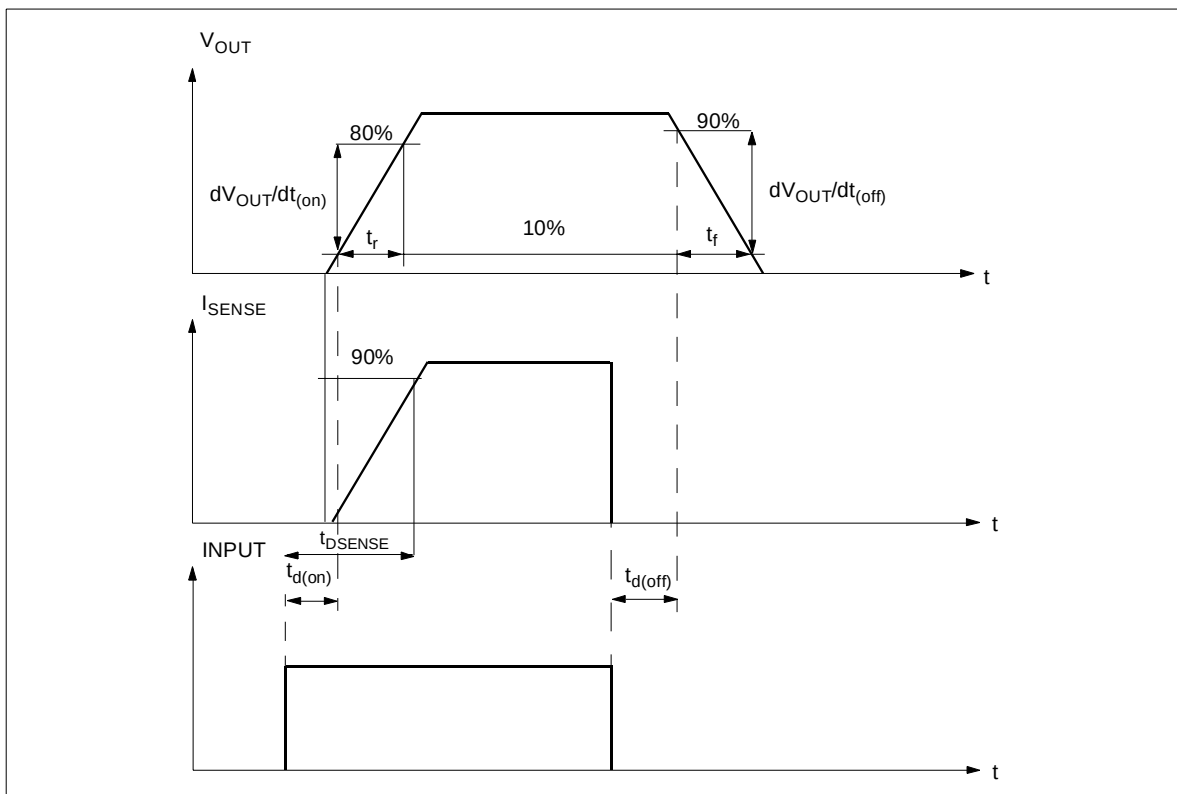
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
K_1	I_{OUT}/I_{SENSE}	$I_{OUT}=1A$; $V_{SENSE}=0.5V$; $T_j = -40^\circ C \dots +150^\circ C$	3300	4400	6000	
dK_1/K_1	Current Sense Ratio Drift	$I_{OUT}=1A$; $V_{SENSE}=0.5V$; $T_j = -40^\circ C \dots +150^\circ C$	-10		+10	%
K_2	I_{OUT}/I_{SENSE}	$I_{OUT}=10A$; $V_{SENSE}=4V$; $T_j = -40^\circ C$ $T_j = 25^\circ C \dots +150^\circ C$	4200 4400	4900 4900	6000 5750	
dK_2/K_2	Current Sense Ratio Drift	$I_{OUT}=10A$; $V_{SENSE}=4V$; $T_j = -40^\circ C \dots +150^\circ C$	-8		+8	%
K_3	I_{OUT}/I_{SENSE}	$I_{OUT}=30A$; $V_{SENSE}=4V$; $T_j = -40^\circ C$ $T_j = 25^\circ C \dots +150^\circ C$	4200 4400	4900 4900	5500 5250	
dK_3/K_3	Current Sense Ratio Drift	$I_{OUT}=30A$; $V_{SENSE}=4V$; $T_j = -40^\circ C \dots +150^\circ C$	-6		+6	%
I_{SENSEO}	Analog Sense Leakage Current	$V_{CC}=6 \dots 16V$; $I_{OUT}=0A$; $V_{SENSE}=0V$; $T_j = -40^\circ C \dots +150^\circ C$	0		10	μA
V_{SENSE}	Max Analog Sense Output Voltage	$V_{CC}=5.5V$; $I_{OUT}=5A$; $R_{SENSE}=10K\Omega$ $V_{CC}>8V$; $I_{OUT}=10A$; $R_{SENSE}=10K\Omega$	2 4			V V
V_{SENSEH}	Sense Voltage in Overtemperature conditions	$V_{CC}=13V$; $R_{SENSE}=3.9K\Omega$		5.5		V
$R_{VSENSEH}$	Analog Sense Output Impedance in Overtemperature Condition	$V_{CC}=13V$; $T_j > T_{TSD}$; Output Open		400		Ω
t_{DSENSE}	Current sense delay response	to 90% I_{SENSE} (see note 2)			500	μs

PROTECTIONS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
T_{TSD}	Shut-down Temperature		150	175	200	$^\circ C$
T_R	Reset Temperature		135			$^\circ C$
T_{hyst}	Thermal Hysteresis		7	15		$^\circ C$
I_{lim}	DC Short Circuit Current	$V_{CC}=13V$ $5V < V_{CC} < 36V$	30	45	75 75	A A
V_{demag}	Turn-off Output Clamp Voltage	$I_{OUT}=2A$; $V_{IN}=0V$; $L=6mH$	$V_{CC}-41$	$V_{CC}-48$	$V_{CC}-55$	V
V_{ON}	Output Voltage Drop Limitation	$I_{OUT}=1A$; $T_j = -40^\circ C \dots +150^\circ C$		50		mV

Note 2: current sense signal delay after positive input slope

Note: sense pin doesn't have to be left floating.

Figure 1: I_{OUT}/I_{SENSE} versus I_{OUT} **Figure 2:** Switching Characteristics (Resistive load $R_L = 1.3\Omega$)

TRUTH TABLE

CONDITIONS	INPUT	OUTPUT	SENSE
Normal operation	L	L	0
	H	H	Nominal
Overtemperature	L	L	0
	H	L	V_{SENSEH}
Undervoltage	L	L	0
	H	L	0
Overvoltage	L	L	0
	H	L	0
Short circuit to GND	L	L	0
	H	L	$(T_j < T_{TSD})$ 0
	H	L	$(T_j > T_{TSD})$ V_{SENSEH}
Short circuit to V_{CC}	L	H	0
	H	H	< Nominal
Negative output voltage clamp	L	L	0

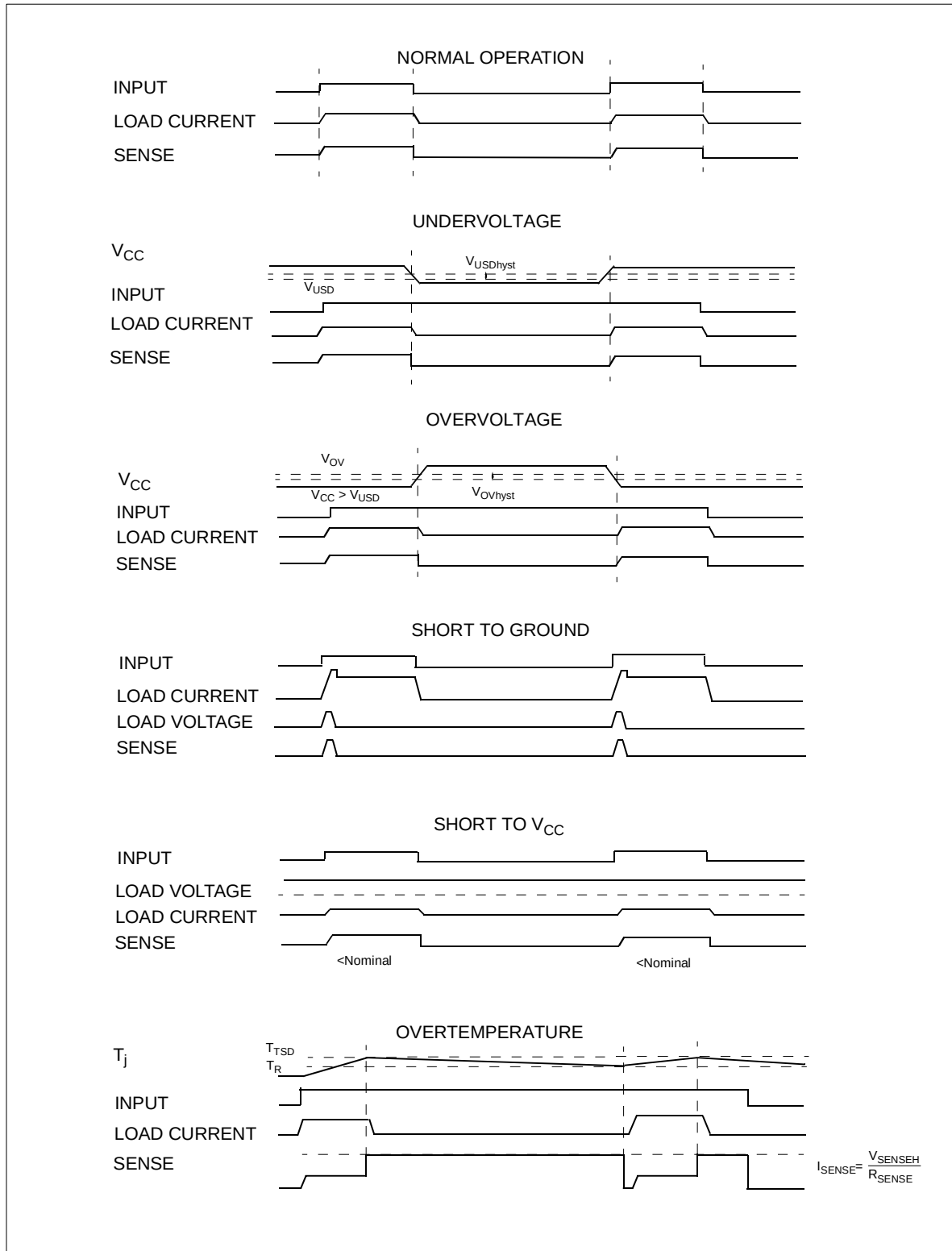
ELECTRICAL TRANSIENT REQUIREMENTS

ISO T/R 7637/1 Test Pulse	TEST LEVELS				
	I	II	III	IV	Delays and Impedance
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 Ω
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 Ω
3a	-25 V	-50 V	-100 V	-150 V	0.1 μ s 50 Ω
3b	+25 V	+50 V	+75 V	+100 V	0.1 μ s 50 Ω
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω

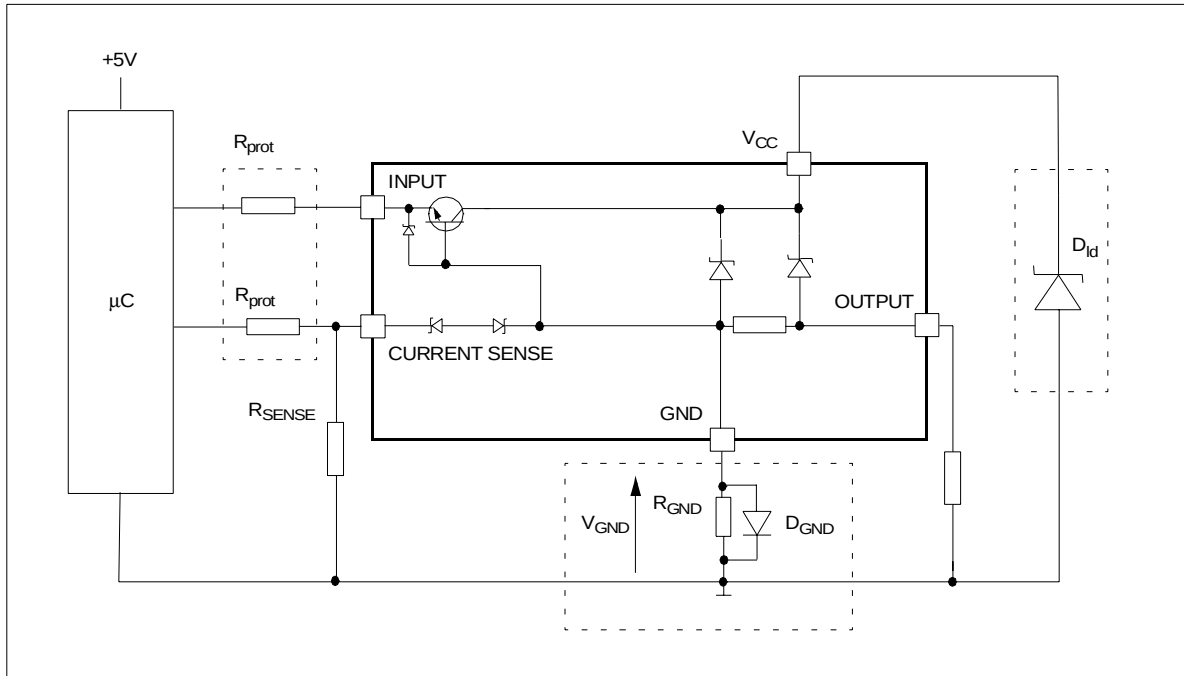
ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULTS			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

Figure 3: Waveforms



APPLICATION SCHEMATIC

**GND PROTECTION NETWORK AGAINST REVERSE BATTERY**

Solution 1: Resistor in the ground line (R_{GND} only). This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

- 1) $R_{GND} \leq 600\text{mV} / (I_{S(on)max})$.
- 2) $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power Dissipation in R_{GND} (when $V_{CC} < 0$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggests to utilize Solution 2 (see below).

Solution 2: A diode (D_{GND}) in the ground line.

A resistor ($R_{GND}=1\text{k}\Omega$) should be inserted in parallel to D_{GND} if the device will be driving an inductive load.

This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift ($\approx 600\text{mV}$) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

LOAD DUMP PROTECTION

D_{Id} is necessary (Voltage Transient Suppressor) if the load dump peak voltage exceeds V_{CC} max DC rating. The same applies if the device will be subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/1 table.

µC I/Os PROTECTION:

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the µC I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of µC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of µC I/Os.

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

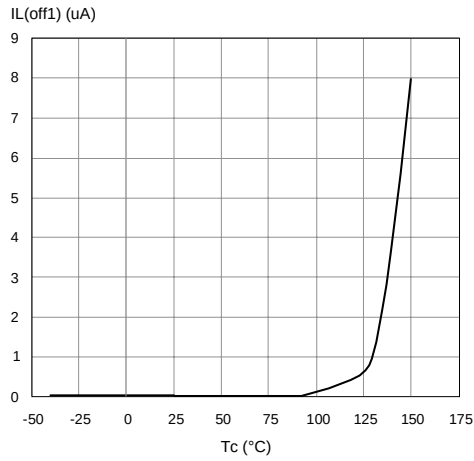
Calculation example:

$$\text{For } V_{CCpeak} = -100\text{V and } I_{latchup} \geq 20\text{mA; } V_{OH\mu C} \geq 4.5\text{V}$$

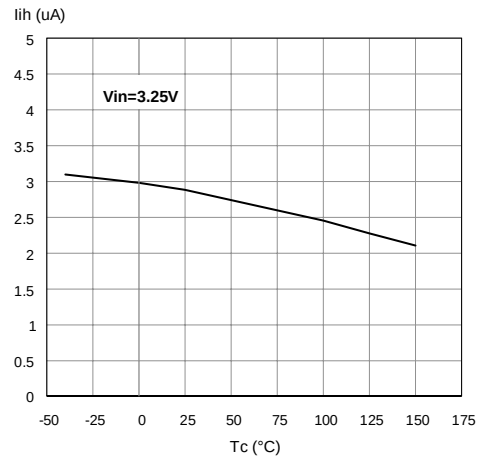
$$5\text{k}\Omega \leq R_{prot} \leq 65\text{k}\Omega.$$

Recommended R_{prot} value is $10\text{k}\Omega$.

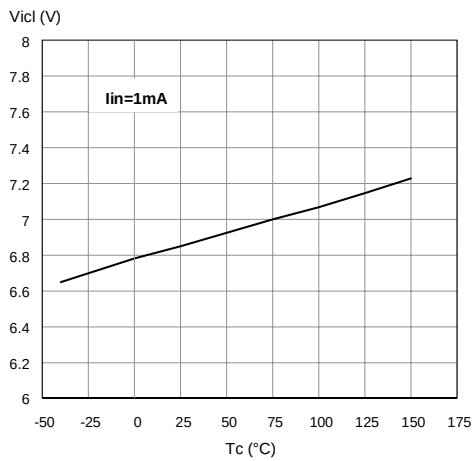
Off State Output Current



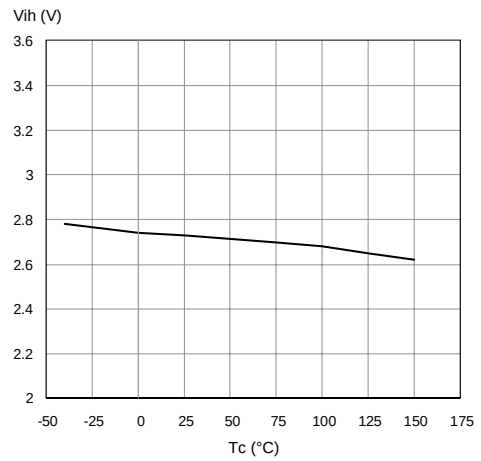
High Level Input Current



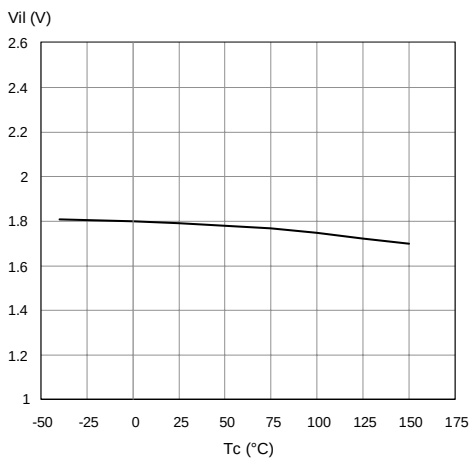
Input Clamp Voltage



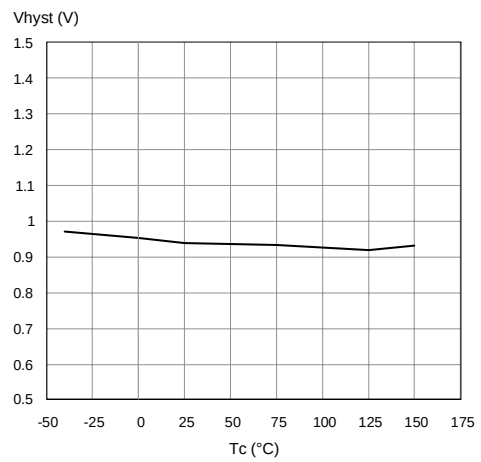
Input High Level



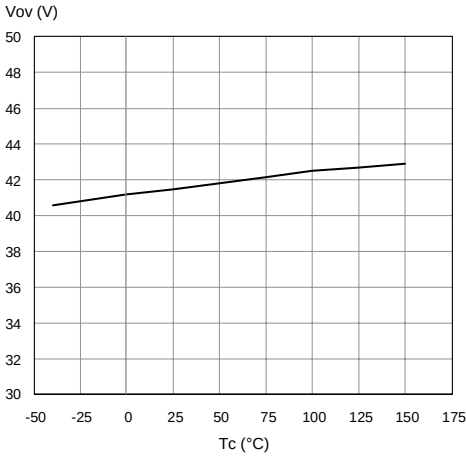
Input Low Level



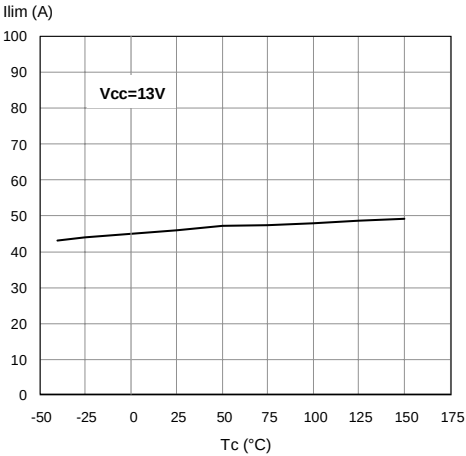
Input Hysteresis Voltage



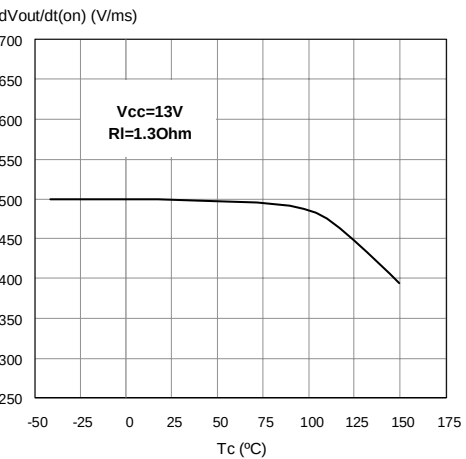
Overvoltage Shutdown



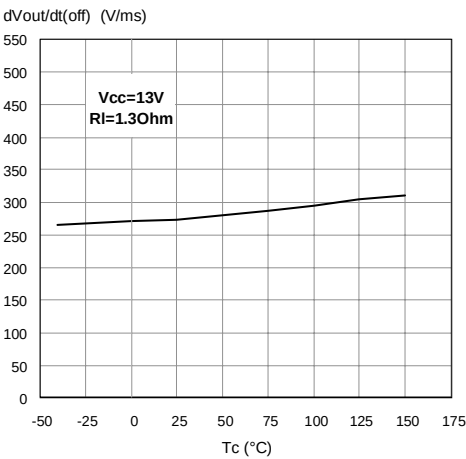
I_{LIM} Vs T_{case}



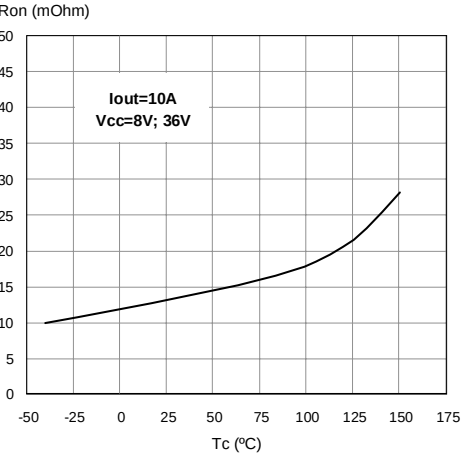
Turn-on Voltage Slope



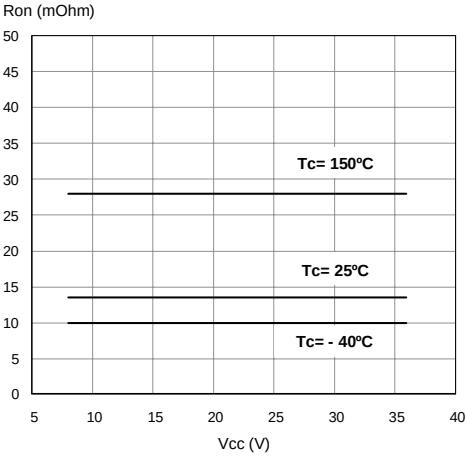
Turn-off Voltage Slope



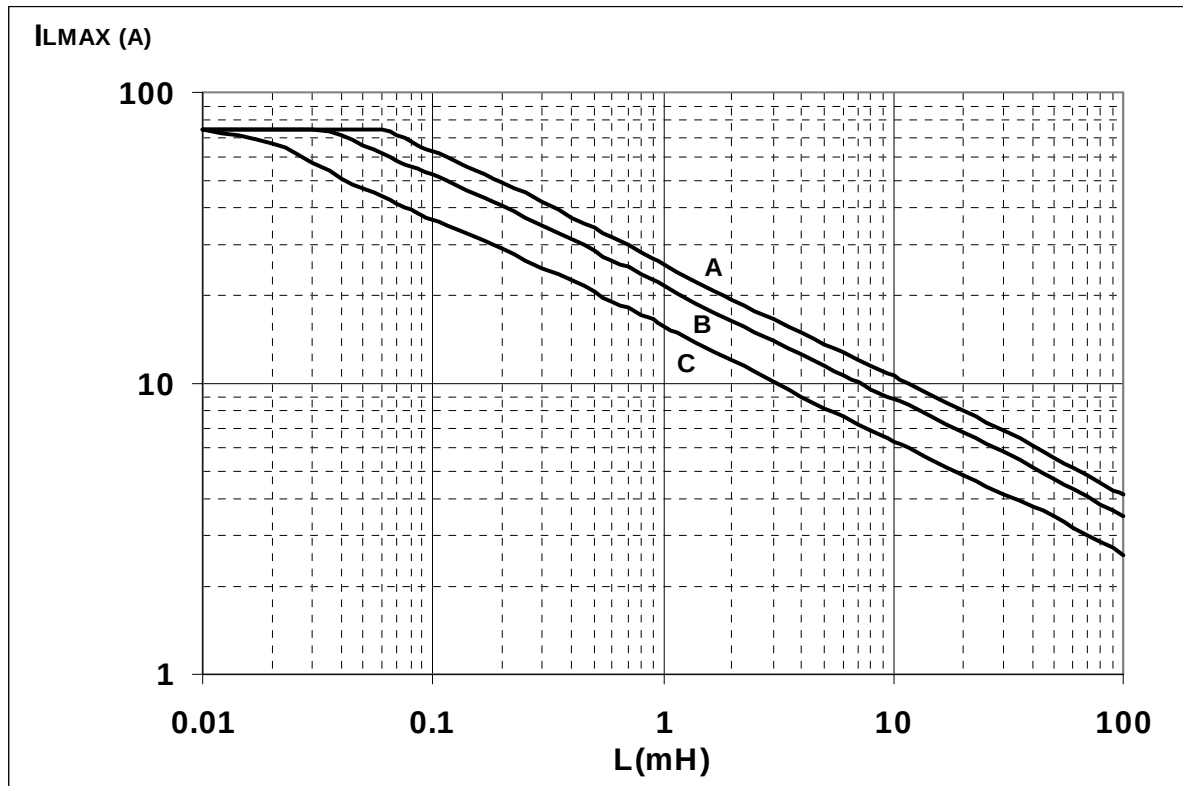
On State Resistance Vs T_{case}



On State Resistance Vs V_{CC}



SO-16L Maximum turn off current versus load inductance



A = Single Pulse at $T_{jstart}=150^{\circ}\text{C}$

B= Repetitive pulse at $T_{jstart}=100^{\circ}\text{C}$

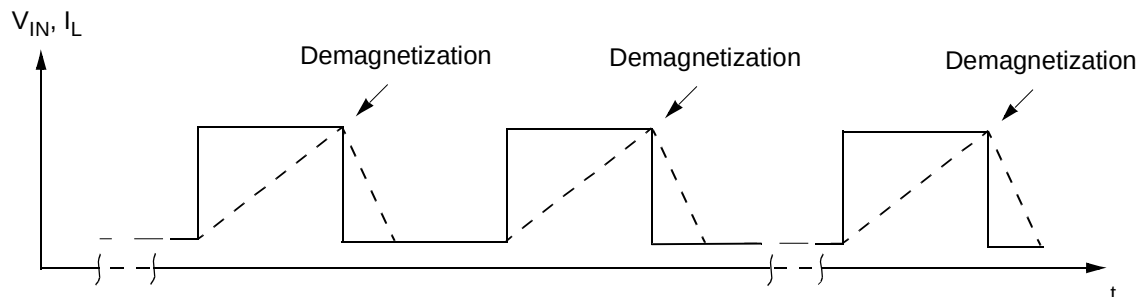
C= Repetitive Pulse at $T_{jstart}=125^{\circ}\text{C}$

Conditions:

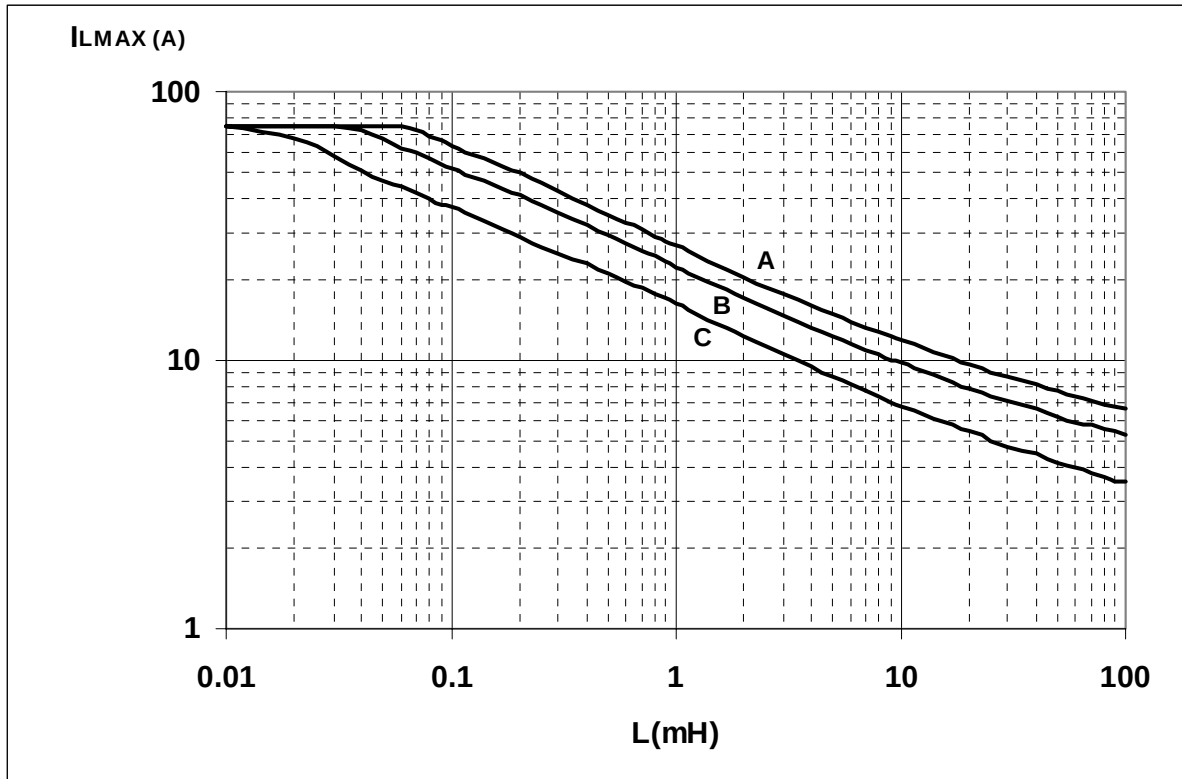
$V_{CC}=13.5\text{V}$

Values are generated with $R_L=0\Omega$

In case of repetitive pulses, T_{jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.



P²PAK Maximum turn off current versus load inductance



A = Single Pulse at $T_{Jstart}=150^{\circ}\text{C}$

B= Repetitive pulse at $T_{Jstart}=100^{\circ}\text{C}$

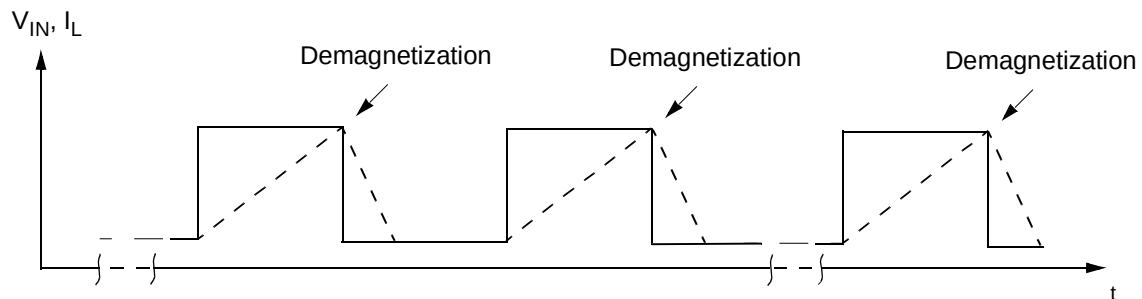
C= Repetitive Pulse at $T_{Jstart}=125^{\circ}\text{C}$

Conditions:

$V_{CC}=13.5\text{V}$

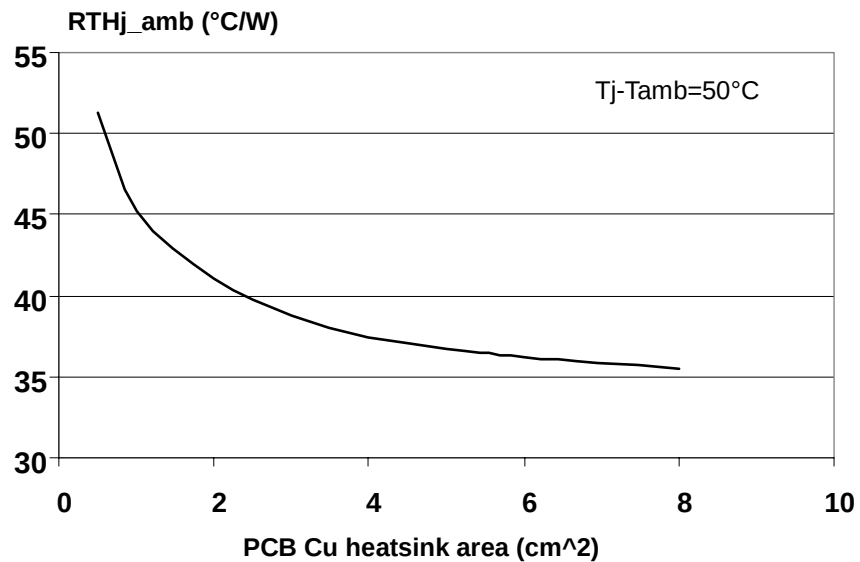
Values are generated with $R_L=0\Omega$

In case of repetitive pulses, T_{Jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.



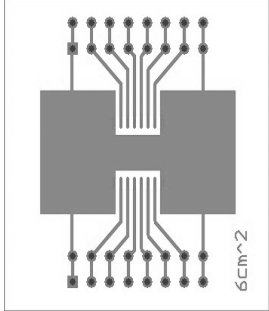
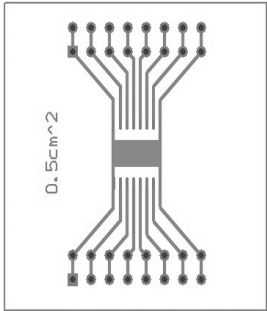
P²PAK THERMAL DATA**P²PAK PC Board**

Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area= 60mm x 60mm, PCB thickness=2mm, Cu thickness=35 μ m, Copper areas: 0.97cm², 8cm²).

 $R_{thj-amb}$ Vs PCB copper area in open box free air condition

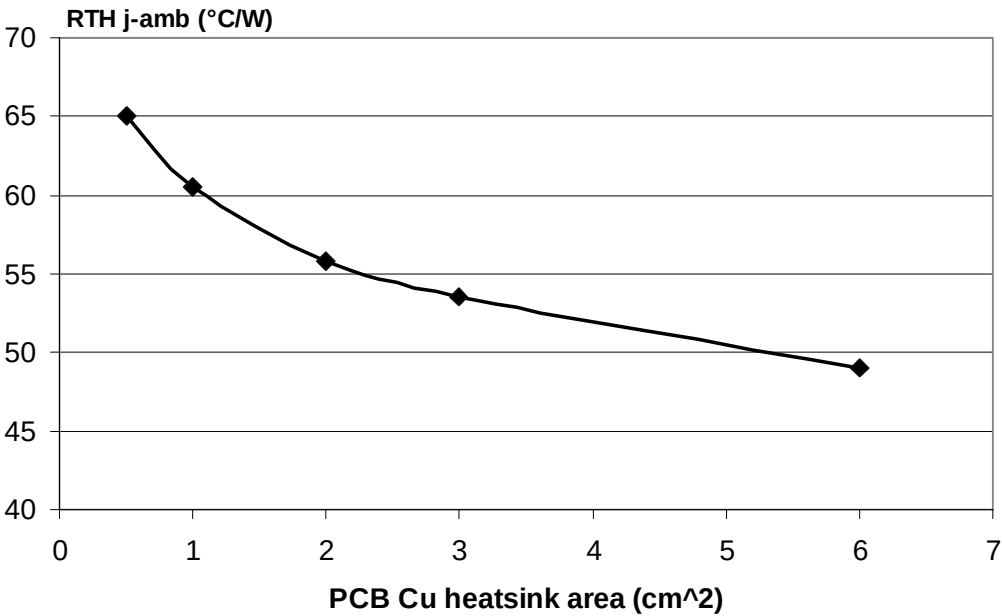
SO-16L THERMAL DATA

SO-16L PC Board

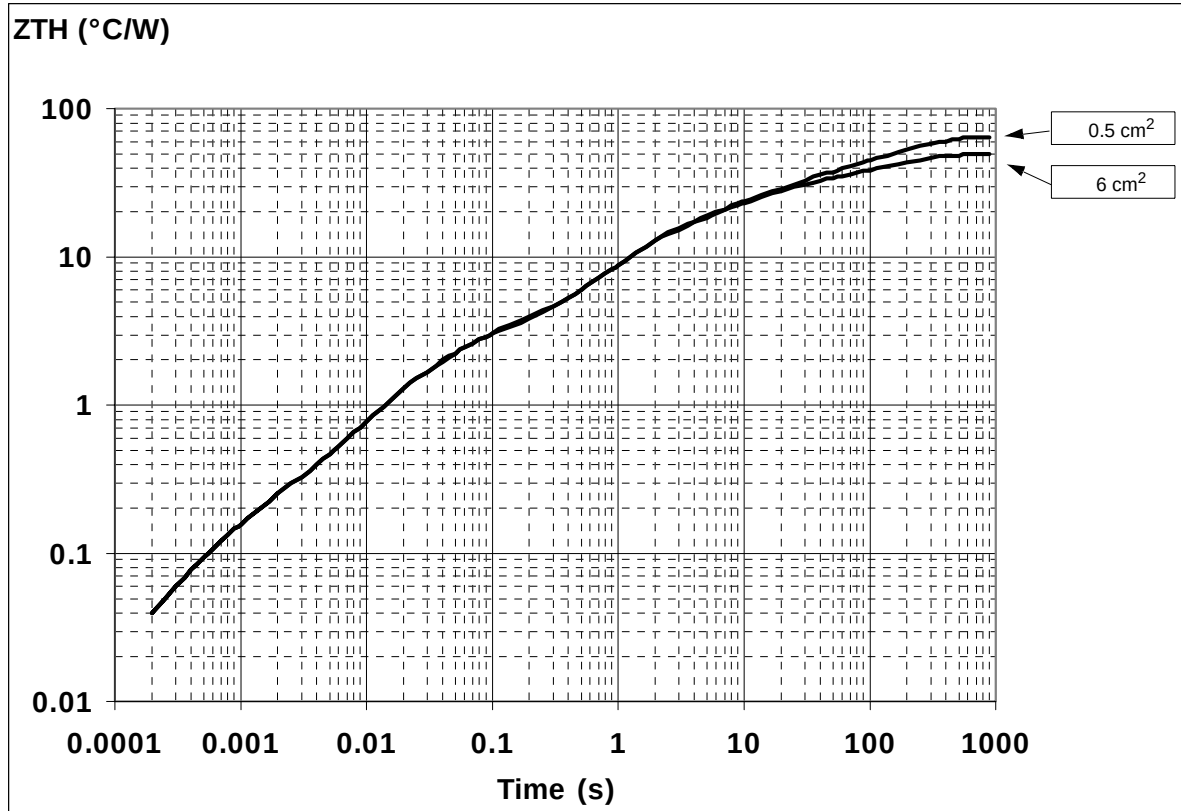


Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area= 41mm x 48mm, PCB thickness=2mm, Cu thickness=35 μ m, Copper areas: 0.5cm², 6cm²).

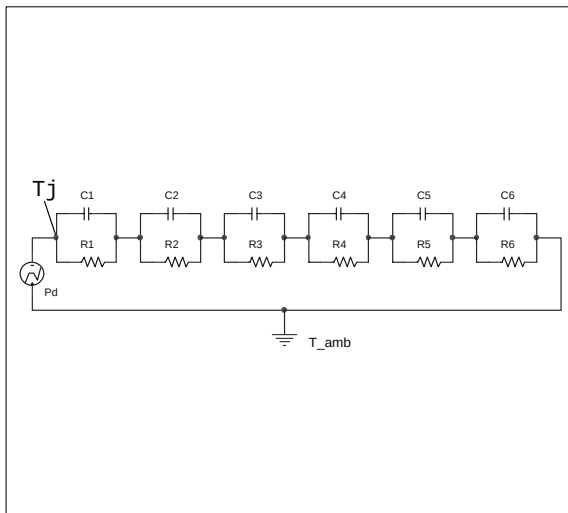
$R_{thj-amb}$ Vs PCB copper area in open box free air condition



SO-16L Thermal Impedance Junction Ambient Single Pulse



Thermal fitting model of a single channel HSD in SO-16L



Pulse calculation formula

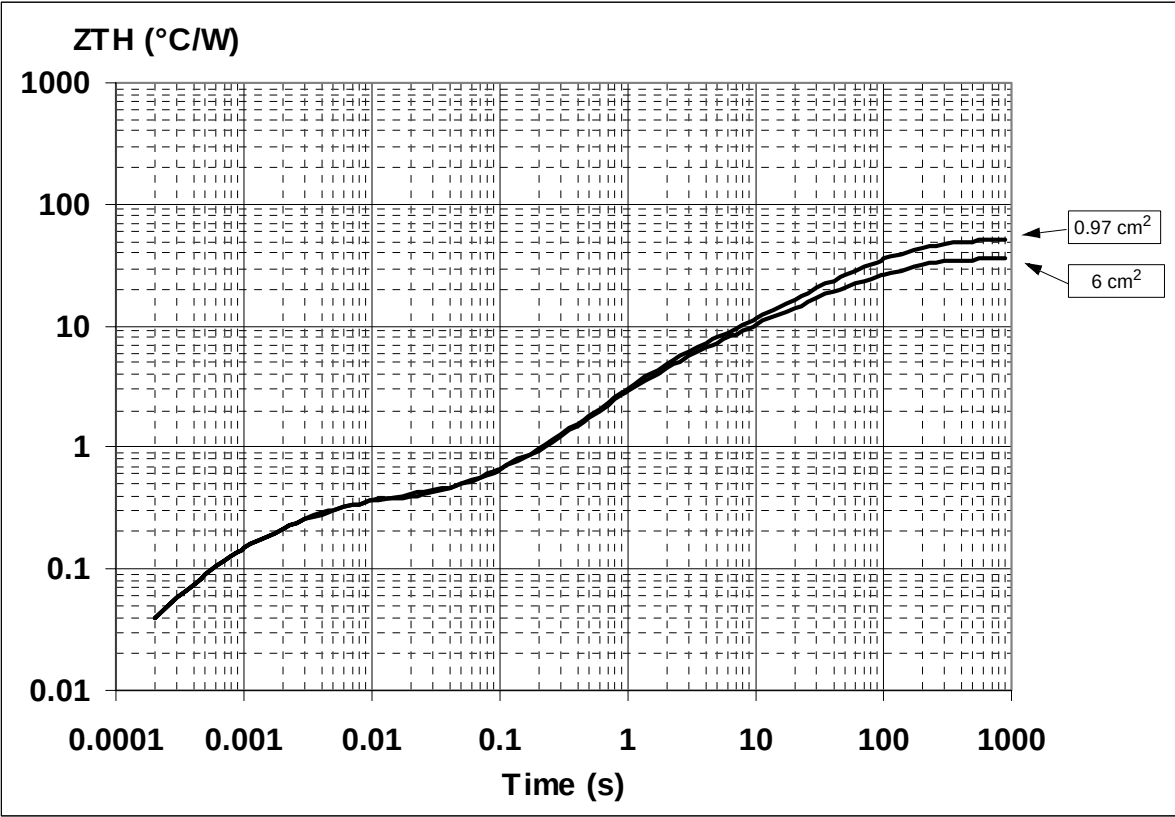
$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p / T$

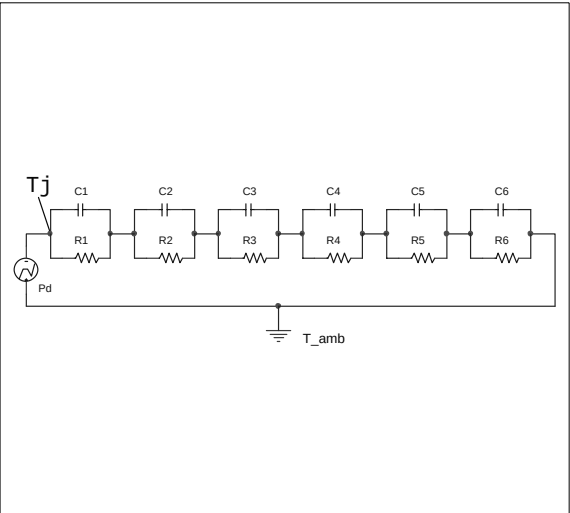
Thermal Parameter

Area/island (cm ²)	0.5	6
R1 (°C/W)	0.02	
R2 (°C/W)	0.1	
R3 (°C/W)	2.2	
R4 (°C/W)	12	
R5 (°C/W)	15	
R6 (°C/W)	35	20
C1 (W.s/°C)	0.0015	
C2 (W.s/°C)	7.00E-03	
C3 (W.s/°C)	1.50E-02	
C4 (W.s/°C)	0.14	
C5 (W.s/°C)	1	
C6 (W.s/°C)	5	8

P²PAK Thermal Impedance Junction Ambient Single Pulse



Thermal fitting model of a single channel HSD in P²PAK



Pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

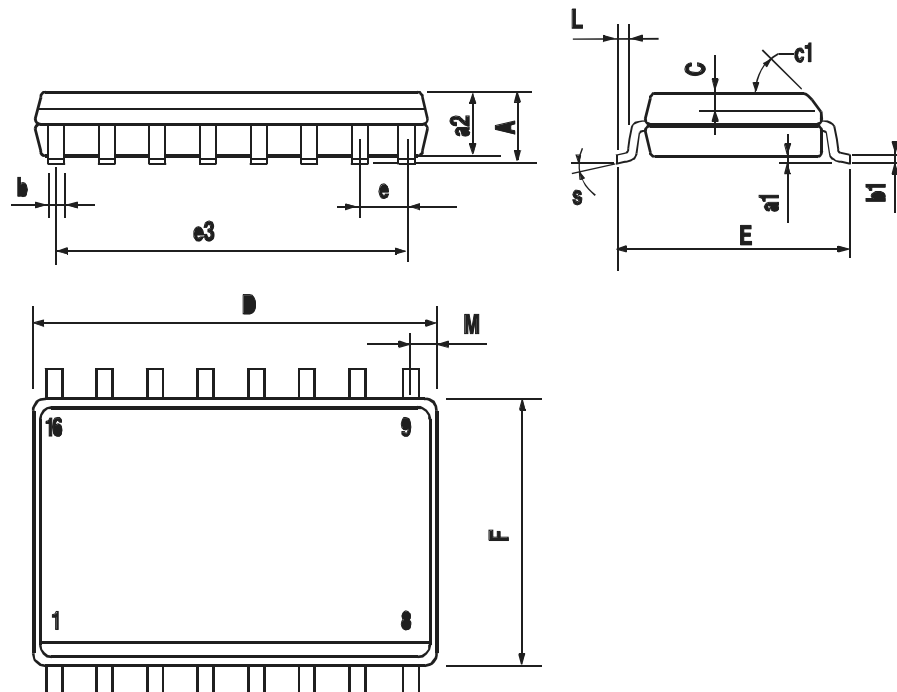
where $\delta = t_p / T$

Thermal Parameter

Area/island (cm ²)	0.97	6
R1 (°C/W)	0.02	
R2 (°C/W)	0.1	
R3 (°C/W)	0.22	
R4 (°C/W)	4	
R5 (°C/W)	9	
R6 (°C/W)	37	22
C1 (W.s/°C)	0.0015	
C2 (W.s/°C)	0.007	
C3 (W.s/°C)	0.015	
C4 (W.s/°C)	0.4	
C5 (W.s/°C)	2	
C6 (W.s/°C)	3	5

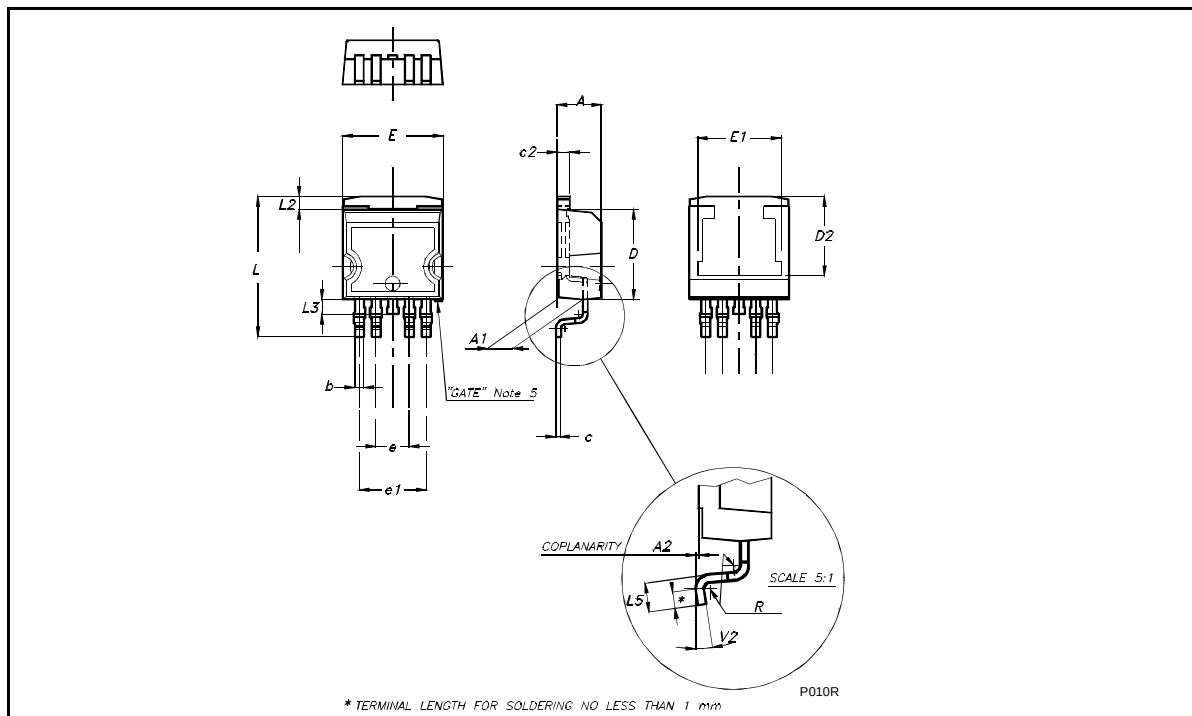
SO-16L MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	10.1		10.5	0.397		0.413
E	10.0		10.65	0.393		0.419
e		1.27			0.050	
e3		8.89			0.350	
F	7.4		7.6	0.291		0.300
L	0.5		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					

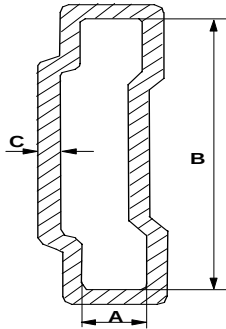


P²PAK MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.30		4.80
A1	2.40		2.80
A2	0.03		0.23
b	0.80		1.05
c	0.45		0.60
c2	1.17		1.37
D	8.95		9.35
D2		8.00	
E	10.00		10.40
E1		8.50	
e	3.20		3.60
e1	6.60		7.00
L	13.70		14.50
L2	1.25		1.40
L3	0.90		1.70
L5	1.55		2.40
R		0.40	
V2	0°		8°
Package Weight	1.40 Gr (typ)		



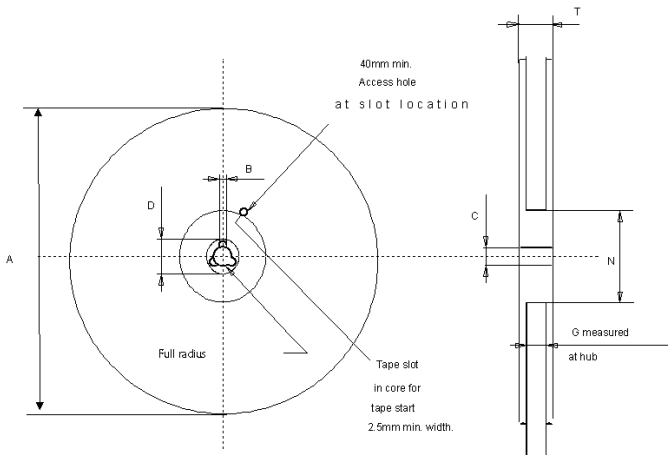
SO-16L TUBE SHIPMENT (no suffix)



Base Q.ty	50
Bulk Q.ty	1000
Tube length (± 0.5)	532
A	3.5
B	13.8
C (± 0.1)	0.6

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

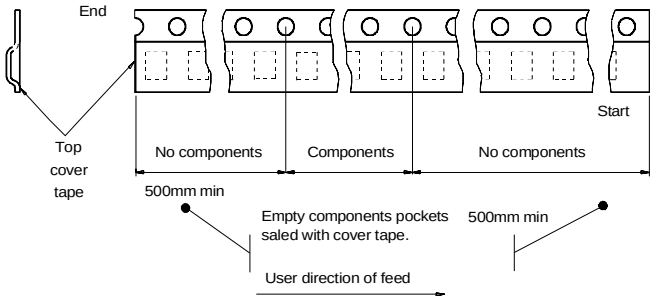
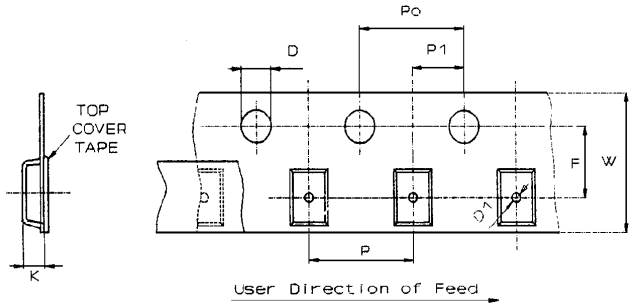
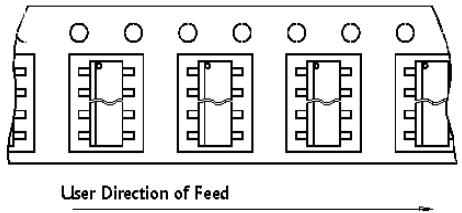
Base Q.ty	1000
Bulk Q.ty	1000
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G ($+ 2 / - 0$)	16.4
N (min)	60
T (max)	22.4

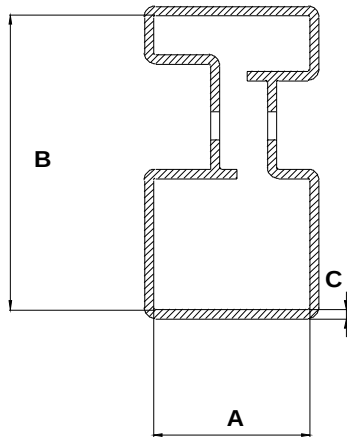
TAPE DIMENSIONS

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	16
Tape Hole Spacing	P0 (± 0.1)	4
Component Spacing	P	12
Hole Diameter	D ($\pm 0.1/-0$)	1.5
Hole Diameter	D1 (min)	1.5
Hole Position	F (± 0.05)	7.5
Compartment Depth	K (max)	6.5
Hole Spacing	P1 (± 0.1)	2

All dimensions are in mm.

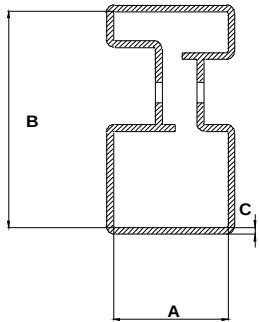


PENTAWATT TUBE SHIPMENT (no suffix)

Base Q.ty	50
Bulk Q.ty	1000
Tube length (± 0.5)	532
A	18
B	33.1
C (± 0.1)	1

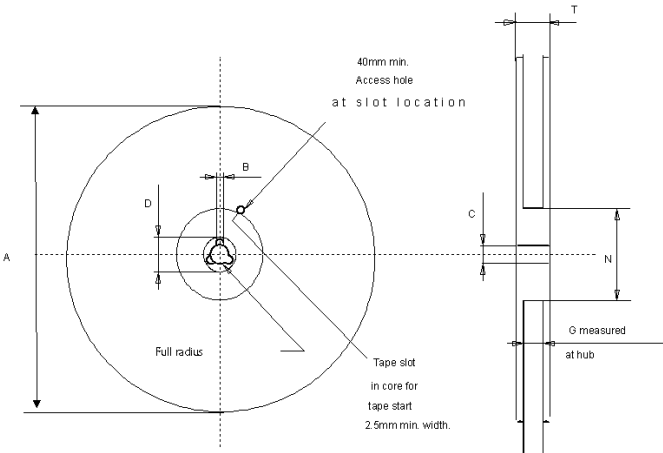
All dimensions are in mm.

P²PAK TUBE SHIPMENT (no suffix)

	Base Q.ty	50
	Bulk Q.ty	1000
	Tube length (± 0.5)	532
	A	18
	B	33.1
	C (± 0.1)	1

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")

	REEL DIMENSIONS	
	Base Q.ty	1000
	Bulk Q.ty	1000
	A (max)	330
	B (min)	1.5
	C (± 0.2)	13
	F	20.2
	G (+ 2 / - 0)	24.4
	N (min)	60
	T (max)	30.4

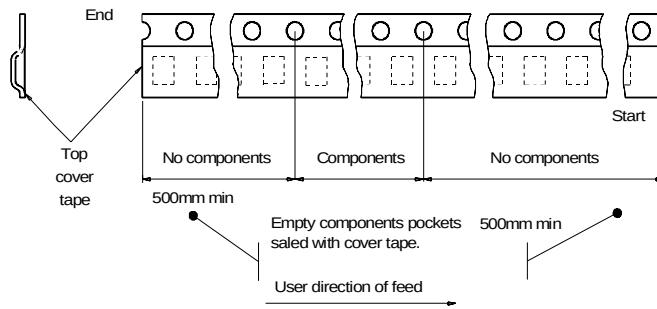
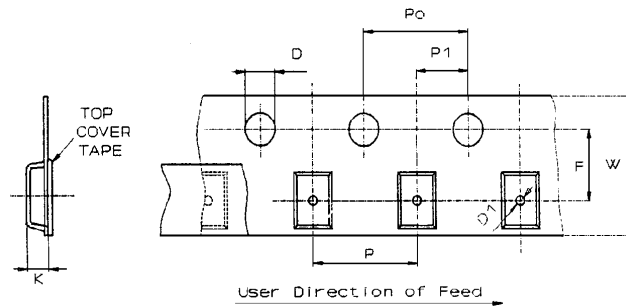
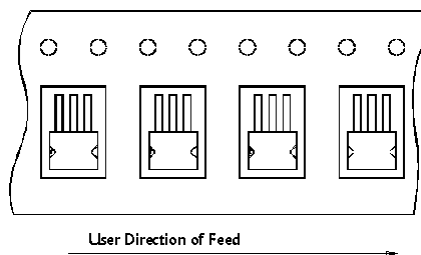
All dimensions are in mm.

TAPE DIMENSIONS

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	24
Tape Hole Spacing	P0 (± 0.1)	4
Component Spacing	P	16
Hole Diameter	D (± 0.1/-0)	1.5
Hole Diameter	D1 (min)	1.5
Hole Position	F (± 0.05)	11.5
Compartment Depth	K (max)	6.5
Hole Spacing	P1 (± 0.1)	2

All dimensions are in mm.



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